

2SA1310

Silicon PNP epitaxial planer type

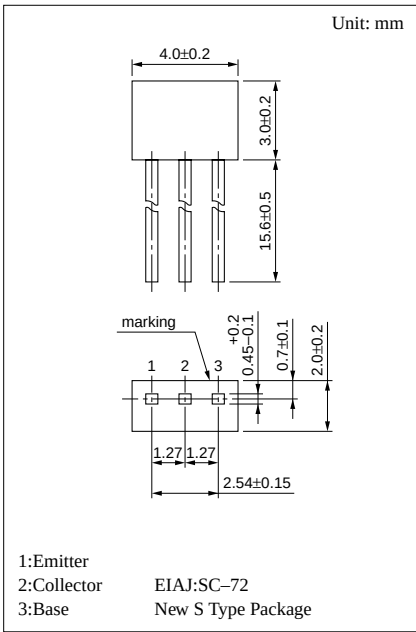
For low-frequency and low-noise amplification
Complementary to 2SC3312

■ Features

- Allowing supply with the radial taping.
- Low noise voltage NV.
- High foward current transfer ratio h_{FE} .
- Optimum for high-density mounting.

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-55	V
Emitter to base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-200	mA
Collector current	I_C	-100	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C



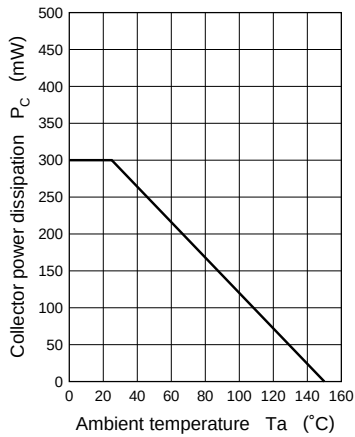
■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -10V, I_E = 0$			-0.1	μA
	I_{CEO}	$V_{CE} = -10V, I_B = 0$			-1	μA
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-60			V
Collector to emitter voltage	V_{CEO}	$I_C = -2mA, I_B = 0$	-55			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-7			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = -5V, I_C = -2mA$	180		700	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.6	V
Base to emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -30mA$			-1	V
Transition frequency	f_T	$V_{CB} = -5V, I_E = 2mA, f = 200MHz$		200		MHz
Noise voltage	NV	$V_{CE} = -10V, I_C = -1mA, G_v = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$			150	mV

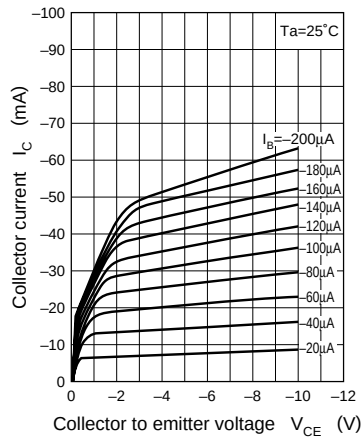
* h_{FE} Rank classification

Rank	R	S	T
h_{FE}	180 ~ 360	260 ~ 520	360 ~ 700

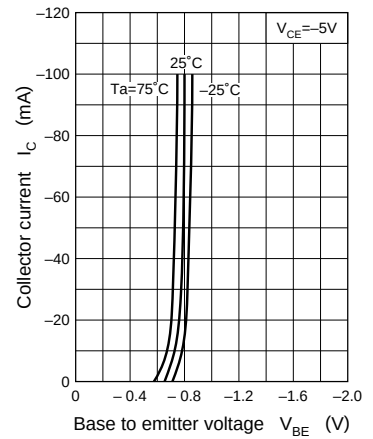
$P_C - T_a$



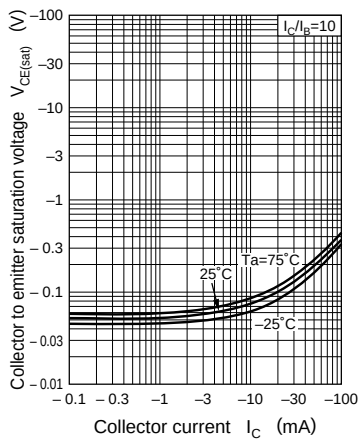
$I_C - V_{CE}$



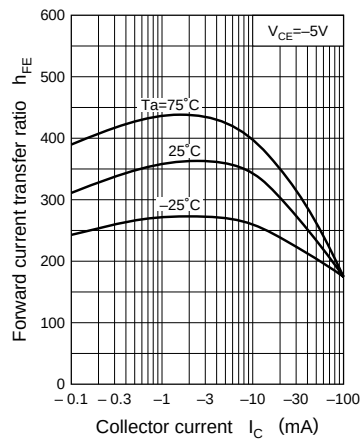
$I_C - V_{BE}$



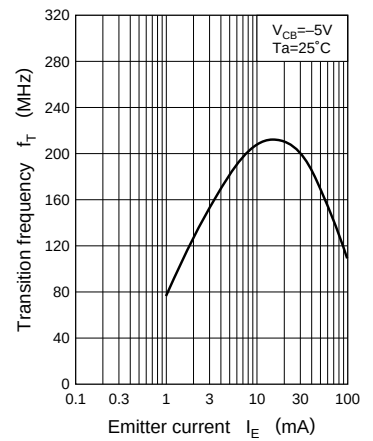
$V_{CE(\text{sat})} - I_C$



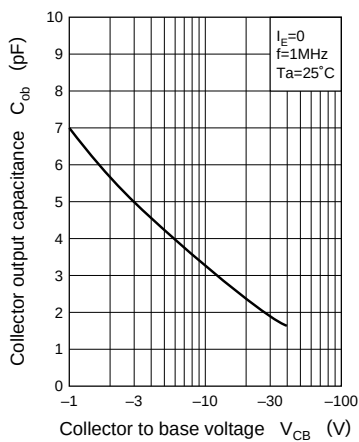
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



$NV - I_C$

